

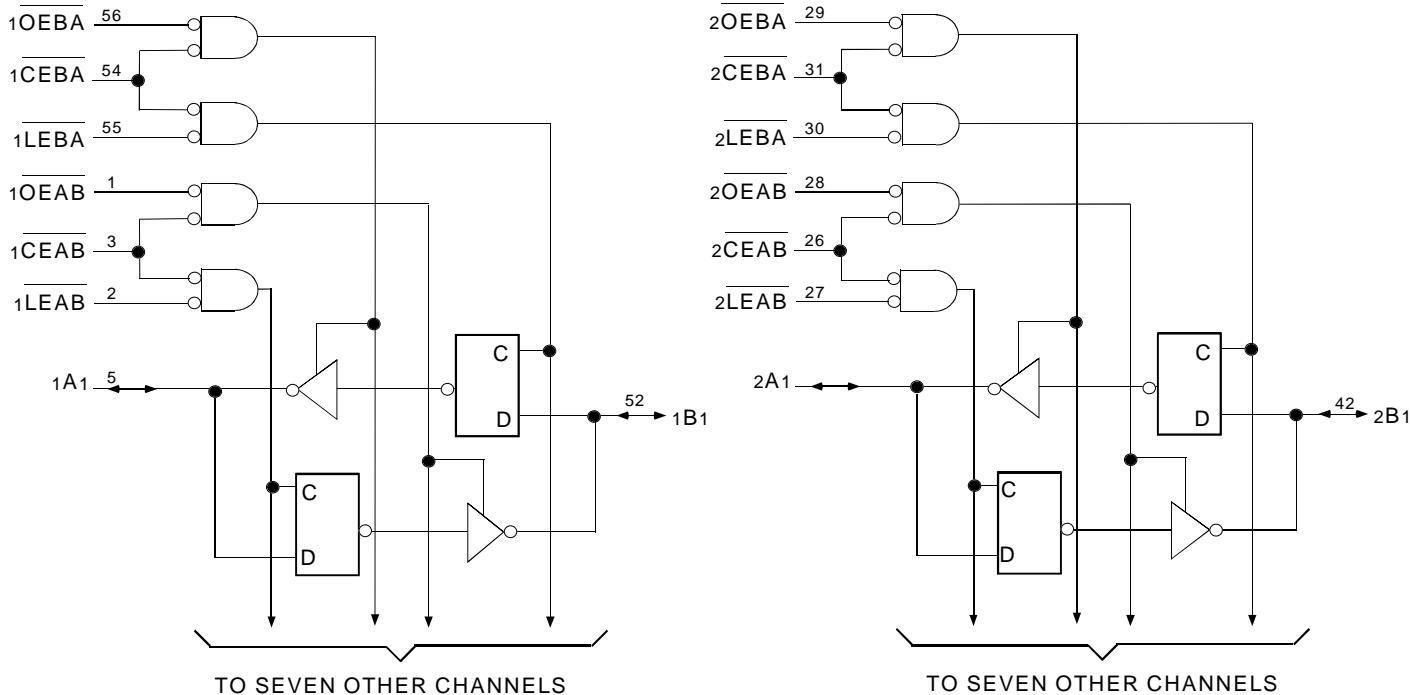
FEATURES:

- 0.5 MICRON CMOS Technology
- Typical $t_{sk(o)}$ (Output Skew) < 250ps
- ESD > 2000V per MIL-STD-883, Method 3015;
> 200V using machine model ($C = 200\text{pF}$, $R = 0$)
- $V_{cc} = 3.3V \pm 0.3V$, Normal Range or $V_{cc} = 2.7V$ to 3.6V, Extended Range
- CMOS power levels ($0.4\mu\text{W}$ typ. static)
- Rail-to-Rail output swing for increased noise margin
- Low Ground Bounce (0.3V typ.)
- Inputs (except I/O) can be driven by 3.3V or 5V components
- Available in SSOP, TSSOP and TVSOP Packages

DESCRIPTION:

The FCT163543/A/C 16-bit latched transceivers are built using advanced dual metal CMOS technology. These high-speed, low-power devices are organized as two independent 8-bit D-type latched transceivers with separate input and output control to permit independent control of data flow in either direction. For example, the A-to-B Enable ($xCEAB$) must be low in order to enter data from the A port or to output data from the B port. $xLEAB$ controls the latch function. When $xLEAB$ is low, the latches are transparent. A subsequent low-to-high transition of $xLEAB$ signal puts the A latches in the storage mode. $xOEAB$ performs output enable function on the B port. Data flow from the B port to the A port is similar but requires using $xCEBA$, $xLEBA$, and $xOEBA$ inputs. Flow-through organization of signal pins simplifies layout. All inputs are designed with hysteresis for improved noise margin.

The FCT163543/A/C have series current limiting resistors. These offer low ground bounce, minimal undershoot, and controlled output fall times—reducing the need for external series terminating resistors.

FUNCTIONAL BLOCK DIAGRAM


PIN CONFIGURATION

1OEAB		1	56		1OEBA
1LEAB		2	55		1LEBA
1CEAB		3	54		1CEBA
GND		4	53		GND
1A1		5	52		1B1
1A2		6	51		1B2
Vcc		7	50		Vcc
1A3		8	49		1B3
1A4		9	48		1B4
1A5		10	47		1B5
GND		11	46		GND
1A6		12	45		1B6
1A7		13	44		1B7
1A8	SO56-1	14	SO56-2	43	1B8
2A1	SO56-3	15	42		2B1
2A2		16	41		2B2
2A3		17	40		2B3
GND		18	39		GND
2A4		19	38		2B4
2A5		20	37		2B5
2A6		21	36		2B6
Vcc		22	35		Vcc
2A7		23	34		2B7
2A8		24	33		2B8
GND		25	32		GND
2CEAB		26	31		2CEBA
2LEAB		27	30		2LEBA
2OEAB		28	29		2OEBA

SSOP/ TSSOP/ TVSOP
TOP VIEW

PIN DESCRIPTION

Pin Names	Description
xOEAB	A-to-B Output Enable Input (Active LOW)
xOEBA	B-to-A Output Enable Input (Active LOW)
xCEAB	A-to-B Enable Input (Active LOW)
xCEBA	B-to-A Enable Input (Active LOW)
xLEAB	A-to-B Latch Enable Input (Active LOW)
xLEBA	B-to-A Latch Enable Input (Active LOW)
xAx	A-to-B Data Inputs or B-to-A 3-State Outputs
xBx	B-to-A Data Inputs or A-to-B 3-State Outputs

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to +7	V
VTERM ⁽⁴⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
TSTG	Storage Temperature	-65 to +150	°C
IOUT	DC Output Current	-60 to +60	mA

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NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- Vcc terminals.
- Input terminals.
- Outputs and I/O terminals.

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
Cin	Input Capacitance	Vin = 0V	3.5	6	pF
Cout	Output Capacitance	Vout = 0V	3.5	8	pF

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NOTE:

- This parameter is measured at characterization but not tested.

FUNCTION TABLE^(1,3)

FOR A-TO-B (SYMMETRIC WITH B-TO-A)

Inputs			Latch Status	Output Buffers
xCEAB	xLEAB	xOEAB	xAx to xBx	xBx
H	X	X	Storing	High Z
X	H	X	Storing	X
L	L	L	Transparent	Current A Inputs
L	H	L	Storing	Previous ⁽²⁾ A Inputs
L	L	H	Transparent	High Z
L	H	H	Storing	High Z

NOTES:

- A-to-B data flow shown; B-to-A flow control is the same, except using xCEBA, xLEBA and xOEBA.
- Before xLEAB LOW-to-HIGH Transition
- H = HIGH Voltage Level
L = LOW Voltage Level
X = Don't Care

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial: $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$, $V_{CC} = 2.7\text{V}$ to 3.6V

Symbol	Parameter	Test Conditions ⁽¹⁾			Min.	Typ. ⁽²⁾	Max.	Unit		
V_{IH}	Input HIGH Level (Input pins)	Guaranteed Logic HIGH Level	2	—	5.5	V	$V_{CC} + 0.5$			
	Input HIGH Level (I/O pins)									
V_{IL}	Input LOW Level (Input and I/O pins)	Guaranteed Logic LOW Level			−0.5	—	0.8	V		
I_{IH}	Input HIGH Current (Input pins)	$V_{CC} = \text{Max.}$	$V_I = 5.5\text{V}$	—	—	± 1	μA			
	Input HIGH Current (I/O pins)									
I_{IL}	Input LOW Current (Input pins)	$V_{CC} = \text{Max.}$	$V_I = \text{GND}$	—	—	± 1	μA			
	Input LOW Current (I/O pins)									
I_{OZH}	High Impedance Output Current (3-State Output pins)	$V_{CC} = \text{Max.}$	$V_O = V_{CC}$	—	—	± 1	μA			
I_{OZL}										
V_{IK}	Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$			—	−0.7	−1.2	V		
I_{ODH}	Output HIGH Current	$V_{CC} = 3.3\text{V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_O = 1.5\text{V}$ ⁽³⁾								
I_{ODL}	Output LOW Current	$V_{CC} = 3.3\text{V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_O = 1.5\text{V}$ ⁽³⁾			50	90	200	mA		
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -0.1\text{mA}$ $I_{OH} = -3\text{mA}$	$V_{CC} - 0.2$	—	—	V			
		$V_{CC} = 3\text{V}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -8\text{mA}$	$2.4^{(5)}$	3	—				
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 0.1\text{mA}$ $I_{OL} = 16\text{mA}$	—	—	0.2	V			
		$V_{CC} = 3\text{V}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 24\text{mA}$	—	0.3	0.55				
I_{OS}	Short Circuit Current ⁽⁴⁾	$V_{CC} = \text{Max.}, V_O = \text{GND}$ ⁽³⁾			−60	−135	−240	mA		
V_H	Input Hysteresis	—								
I_{CCL} I_{CCH} I_{CCZ}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}$ $V_{IN} = \text{GND or } V_{CC}$			—	0.1	10	μA		

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NOTES:

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 3.3\text{V}$, $+25^\circ\text{C}$ ambient.
- Not more than one output should be tested at one time. Duration of the test should not exceed one second.
- This parameter is guaranteed but not tested.
- $V_{OH} = V_{CC} - 0.6\text{V}$ at rated current.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit	
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = V_{CC} - 0.6V^{(3)}$		—	2	30	μA	
I_{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}, \text{Outputs Open}$ $x\bar{CEAB}$ and $x\bar{OEAB} = \text{GND}$ $x\bar{CEBA} = V_{CC}$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	60	100	$\mu A / MHz$	
I_C	Total Power Supply Current ⁽⁵⁾	$V_{CC} = \text{Max.}, \text{Outputs Open}$ $f_i = 10MHz$ 50% Duty Cycle $x\bar{LEAB}$, $x\bar{CEAB}$ and $x\bar{OEAB} = \text{GND}$ $x\bar{CEBA} = V_{CC}$ One Bit Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.6	1	mA	
			$V_{IN} = V_{CC} - 0.6V$ $V_{IN} = \text{GND}$	—	0.6	1		
		$V_{CC} = \text{Max.}, \text{Outputs Open}$ $f_i = 2.5MHz$ 50% Duty Cycle $x\bar{LEAB}$, $x\bar{CEAB}$ and $x\bar{OEAB} = \text{GND}$ $x\bar{CEBA} = V_{CC}$ Sixteen Bits Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	2.4	$4^{(5)}$		
			$V_{IN} = V_{CC} - 0.6V$ $V_{IN} = \text{GND}$	—	2.4	$4.3^{(5)}$		

NOTES:

1. For conditions shown as max. or min., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at $V_{CC} = 3.3V$, $+25^\circ C$ ambient.

3. Per TTL driven input; all other inputs at V_{CC} or GND.

4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.

5. Values for these conditions are examples of the I_C formula. These limits are guaranteed but not tested.

6. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

$$I_C = I_{CC} + D_{HNT} + I_{CCD} (f_{CP}N_{CP}/2 + f_iN_i)$$

I_{CC} = Quiescent Current (I_{CL} , I_{CH} and I_{CZ})

ΔI_{CC} = Power Supply Current for a TTL High Input

D_H = Duty Cycle for TTL Inputs High

N_t = Number of TTL Inputs at D_H

I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

N_{CP} = Number of Clock Inputs at f_{CP}

f_i = Input Frequency

N_i = Number of Inputs at f_i

SWITCHING CHARACTERISTICS OVER OPERATING RANGE (4)

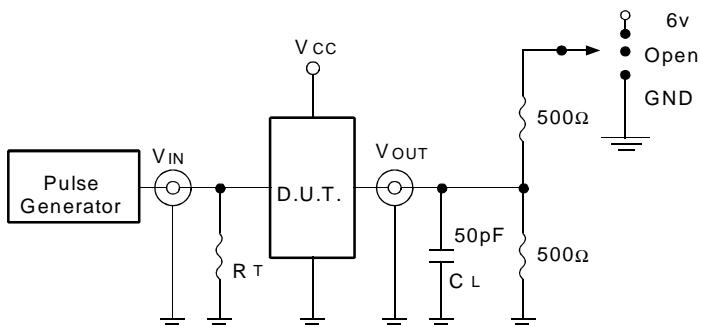
Symbol	Parameter	Condition ⁽¹⁾	FCT163543		FCT163543A		FCT163543C		Unit
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
t_{PLH} t_{PHL}	Propagation Delay Transparent Mode xAx to xBx or xBx to xAx	$C_L = 50\text{pF}$ $R_L = 500\Omega$	1.5	8.5	1.5	6.5	1.5	5.3	ns
	Propagation Delay $x\overline{LEBA}$ to xAx , $x\overline{LEAB}$ to xBx		1.5	12.5	1.5	8	1.5	7	ns
	Output Enable Time $x\overline{OEBA}$ or $x\overline{OEAB}$ to xAx or xBx $x\overline{CEBA}$ or $x\overline{CEAB}$ to xAx or xBx		1.5	12	1.5	9	1.5	8	ns
	Output Disable Time $x\overline{OEBA}$ or $x\overline{OEAB}$ to xAx or xBx $x\overline{CEBA}$ or $x\overline{CEAB}$ to xAx or xBx		1.5	9	1.5	7.5	1.5	6.5	ns
	Set-up Time HIGH or LOW xAx or xBx to $x\overline{LEAB}$ or $x\overline{LEBA}$		3	—	2	—	2	—	ns
	Hold Time HIGH or LOW xAx or xBx to $x\overline{LEAB}$ or $x\overline{LEBA}$		2	—	2	—	2	—	ns
	t_w $x\overline{LEBA}$ or $x\overline{LEAB}$ Pulse Width LOW		5	—	5	—	5	—	ns
	Output Skew ⁽³⁾		—	0.5	—	0.5	—	0.5	ns

NOTES:

1. See test circuits and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.
4. Propagation Delays and Enable/Disable times are with $V_{CC} = 3.3V \pm 0.3V$, Normal Range. For $V_{CC} = 2.7V$ to $3.6V$, Extended Range, all Propagation Delays and Enable/Disable times should be degraded by 20%.

TEST CIRCUITS AND WAVEFORMS

TEST CIRCUITS FOR ALL OUTPUTS



SWITCH POSITION

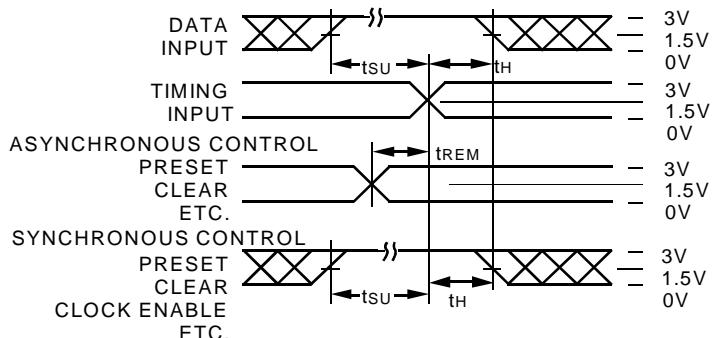
Test	Switch
Open Drain	
Disable Low	6V
Enable Low	
Disable High	GND
Enable High	
All Other Tests	Open

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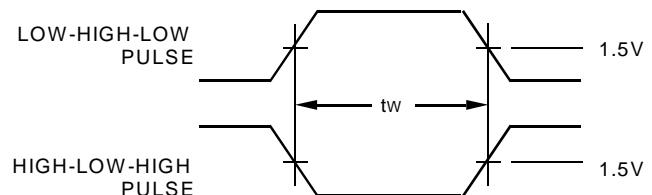
DEFINITIONS:

C_L = Load capacitance: includes jig and probe capacitance.
 R_T = Termination resistance: should be equal to Z_{out} of the Pulse Generator.

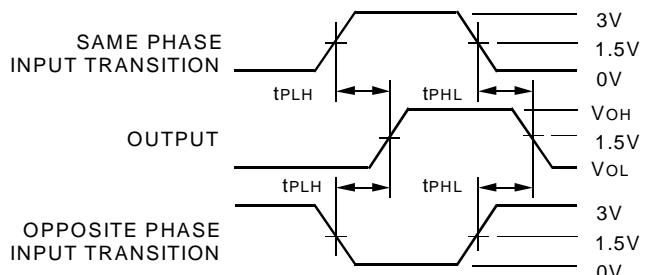
SET-UP, HOLD, AND RELEASE TIMES



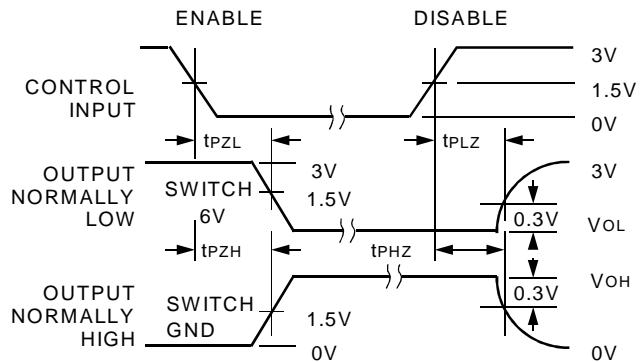
PULSE WIDTH



PROPAGATION DELAY



ENABLE AND DISABLE TIMES



NOTES:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
2. Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $t_f \leq 2.5\text{ns}$; $t_r \leq 2.5\text{ns}$.
3. If V_{cc} is below 3V, input voltage swings should be adjusted not to exceed V_{cc} .

ORDERING INFORMATION

IDT	XX	FCT	XXX	XXXX	X	
Temp. Range		Family		Device Type	Package	
					PV	Shrink Small Outline Package (SO56-1)
					PA	Thin Shrink Small Outline Package (SO56-2)
					PF	Thin Very Small Outline Package (SO56-3)
					543	16-Bit Latched Transceiver
					543A	
					543C	
					163	Double-Density 3.3 Volt
					74	-40°C to +85°C



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